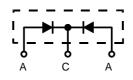


HiPerFRED™ Epitaxial Diode with common cathode and soft recovery

 $I_{FAV} = 2x 5 A$ $V_{RRM} = 200 V$ $t_{rr} = 25 ns$

V _{RSM}	V _{RRM}	Туре
200	200	DSEC 10-02A

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TO-220 AB



A = Anode, C = Cathode, TAB = Cathode

Conditions	Maximum Ratings	
	35	A
$T_c = 160$ °C; rectangular, d = 0.5	5	Α
t_P < 10 μs ; rep. rating, pulse width limited by T_{VJM}	tbd	Α
$T_{VJ} = 45$ °C; $t_p = 10$ ms (50 Hz), sine	80	Α
$T_{VJ} = 25$ °C; non-repetitive $I_{AS} = 2$ A; L = 180 μ H	0.5	mJ
$V_A = 1.5 \text{-} V_R \text{ typ.}; f = 10 \text{ kHz}; repetitive}$	0.2	Α
-5	55+175	°C
	175	°C
-5	55+150	°C
T _C = 25°C	60	W
mounting torque	0.40.6	Nm
typical	2	g
	T_{C} = 160°C; rectangular, d = 0.5 t_{p} < 10 μ s; rep. rating, pulse width limited by T_{VJM} T_{VJ} = 45°C; t_{p} = 10 ms (50 Hz), sine T_{VJ} = 25°C; non-repetitive I_{AS} = 2 A; L = 180 μ H V_{A} = 1.5· V_{R} typ.; f = 10 kHz; repetitive -5 T_{C} = 25°C mounting torque	$T_{\text{C}} = 160^{\circ}\text{C}; \text{ rectangular, d} = 0.5 \\ t_{\text{P}} < 10 \ \mu\text{s}; \text{ rep. rating, pulse width limited by } T_{\text{VJM}} \\ \text{tbd} \\ T_{\text{VJ}} = 45^{\circ}\text{C}; t_{\text{p}} = 10 \ \text{ms (50 Hz), sine} \\ R_{\text{NS}} = 25^{\circ}\text{C}; \text{ non-repetitive} \\ R_{\text{AS}} = 2 \ \text{A}; \ L = 180 \ \mu\text{H} \\ \text{V}_{\text{A}} = 1.5 \text{-V}_{\text{R}} \text{typ.}; \ f = 10 \ \text{kHz}; \ \text{repetitive} \\ R_{\text{NS}} = 25^{\circ}\text{C}; \text{ non-repetitive} \\ R_{\text{NS}} = 2 \ \text{C}; \text{ non-repetitive} \\ $

Symbol	Conditions	Characteristic Values		
		typ.	max.	
I _R ①	$T_{VJ} = 25^{\circ}C$ $V_{R} = V_{RRM}$ $T_{VJ} = 150^{\circ}C$ $V_{R} = V_{RRM}$		50 0.2	μA mA
V _F 2	$I_F = 5 \text{ A};$ $T_{VJ} = 150^{\circ}\text{C}$ $T_{VJ} = 25^{\circ}\text{C}$		0.81 1.23	V V
R _{thJC} R _{thCH}		0.5	2.5	K/W K/W
t _{rr}	$I_F = 1 \text{ A}$; -di/dt = 50 A/ μ s; $V_R = 30 \text{ V}$; $T_{VJ} = 25^{\circ}\text{C}$	25		ns
I _{RM}	$V_R = 100 \text{ V}; \ I_F = 10 \text{ A}; \ -di_F/dt = 100 \text{ A}/\mu\text{s}$ $T_{VJ} = 100^{\circ}\text{C}$		2.0	А

Features

- · International standard package
- · Planar passivated chips
- Very short recovery time
- · Extremely low switching losses
- Low I_{RM}-values
- · Soft recovery behaviour
- Epoxy meets UL 94V-0

Applications

- Antiparallel diode for high frequency switching devices
- · Antisaturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- · Inductive heating
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Advantages

- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{RM} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Dimensions see outlines.pdf

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %

@ Pulse Width = 300 $\mu s,$ Duty Cycle < 2.0 %

Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, test conditions and dimensions.

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